

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A two-beam semiconductor laser device comprising:

a two-beam semiconductor element having [[a]] first and [[a]] second semiconductor laser elements that can be driven independently and that are formed integrally on a substrate; and

a submount having, mounted on a front part thereof, the two-beam semiconductor laser element with a light-emitting face thereof directed forward and having [[a]] first and [[a]] second electrode pads connected to electrodes of the first and second semiconductor laser ~~element~~ elements by being kept in contact therewith,

wherein no photodetector is provided behind the two-beam semiconductor laser element on the submount, and

wherein the first and second electrode pads are formed to extend farther behind the two-beam semiconductor laser element, and are wire-bonded behind the two-beam semiconductor laser element.

2. (Original) The two-beam semiconductor laser device of claim 1,

wherein the first and second electrode pads are wire-bonded at a rear end of the submount.

3. (Previously Presented) The two-beam semiconductor laser device of claim 1,

wherein a distance from the rear end of the two-beam semiconductor laser element to a position where the first and second electrode pads are wire-bonded is 300  $\mu\text{m}$  or shorter.

4. (Previously Presented) The two-beam semiconductor laser device of claim 1,  
wherein a lateral length of the submount is 400  $\mu\text{m}$  or more but 700  $\mu\text{m}$  or less.
5. (Previously Presented) The two-beam semiconductor laser device of claim 1,  
wherein the submount is mounted in a package composed of a frame and a resin member.
6. (Original) The two-beam semiconductor laser device of claim 5,  
wherein the two-beam semiconductor laser device is built as a three-terminal two-beam semiconductor laser device having three terminals.